DDTC (R1-ONLY SERIES) UA

NPN PRE-BIASED SMALL SIGNAL SURFACE MOUNT TRANSISTOR

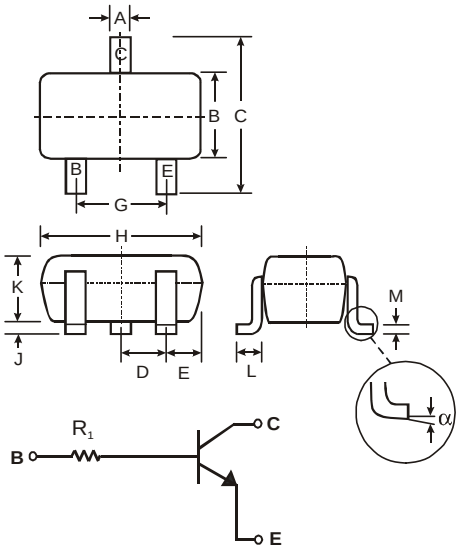
Features

- Epitaxial Planar Die Construction
- Complementary PNP Types Available (DDTA)
- Built-In Biasing Resistor, R1 only
- **Lead Free/RoHS Compliant (Note 2)**
- **"Green" Device (Note 3 and 4)**

Mechanical Data

- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound, Note 4. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Marking Information: See Diagrams & Page 3
- Type Code: See Table Below
- Ordering Information: See Page 3
- Weight: 0.006 grams (approximate)

P/N	R1 (NOM)	Type Code
DDTC113TUA	1KΩ	N01
DDTC123TUA	2.2KΩ	N03
DDTC143TUA	4.7KΩ	N07
DDTC114TUA	10KΩ	N12
DDTC124TUA	22KΩ	N16
DDTC144TUA	47KΩ	N19
DDTC115TUA	100KΩ	N23
DDTC125TUA	200KΩ	N25



SCHEMATIC DIAGRAM

SOT-323		
Dim	**Min**	**Max**
A	0.25	0.40
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
E	0.30	0.40
G	1.20	1.40
H	1.80	2.20
J	0.0	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.18
α	0°	8°
All Dimensions in mm		

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C (Max)	100	mA
Power Dissipation	P_d	200	mW
Thermal Resistance, Junction to Ambient Air (Note 1)	$R_{\theta JA}$	833	°C/W
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	°C

Notes:
1. Mounted on FR4 PC Board with recommended pad layout as shown on Diodes Inc., suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf
2. No purposefully added lead.
3. Diodes Inc.'s "Green" Policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
4. Product manufactured with date code 0627 (week 27, 2006) and newer are built with Green Molding Compound. Product manufactured prior to date code 0627 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	50	—	—	V	I_C = 50μA
Collector-Emitter Breakdown Voltage	BV_{CEO}	50	—	—	V	I_C = 1mA
Emitter-Base Breakdown Voltage	BV_{EBO}	5	—	—	V	I_E = 50μA
Collector Cutoff Current	I_{CBO}	—	—	0.5	μA	V_{CB} = 50V
Emitter Cutoff Current	I_{EBO}	—	—	0.5	μA	V_{EB} = 4V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	—	0.3	V	I_C/I_B = 10mA/1mA DDTC113TUA I_C/I_B = 5mA/0.5mA DDTC123TUA I_C/I_B = 2.5mA/.25mA DDTC143TUA I_C/I_B = 1mA/.1mA DDTC114TUA I_C/I_B = 5mA/0.5mA DDTC124TUA I_C/I_B = 2.5mA/.25mA DDTC144TUA I_C/I_B = 1mA/0.1mA DDTC115TUA I_C/I_B = .5mA/.05mA DDTC125TUA
DC Current Transfer Ratio	h_{FE}	100	250	600	—	I_C = 1mA, V_{CE} = 5V
Input Resistor (R_1) Tolerance	ΔR_1	-30	—	+30	%	—
Gain-Bandwidth Product*	f_T	—	250	—	MHz	V_{CE} = 10V, I_E = -5mA, f = 100MHz

*Transistor - For Reference Only

Typical Curves – DDTC114TUA

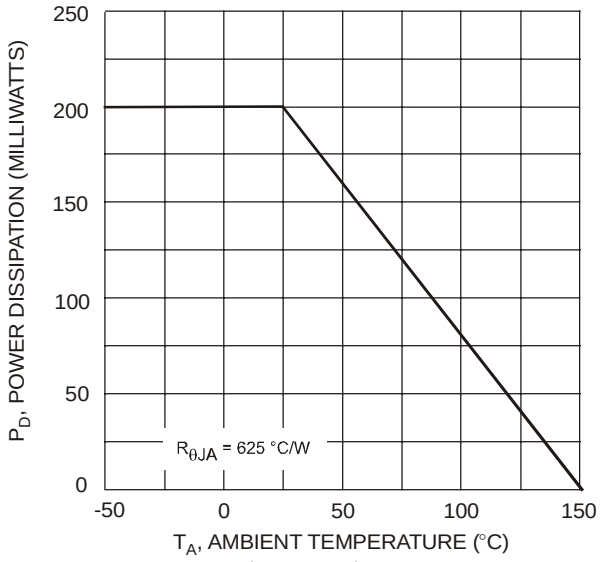


Fig. 1 Derating Curve

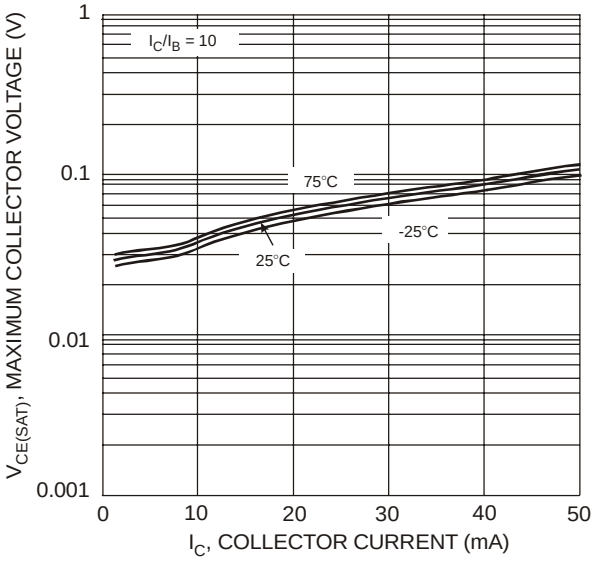


Fig. 2 $V_{CE(SAT)}$ vs. I_C

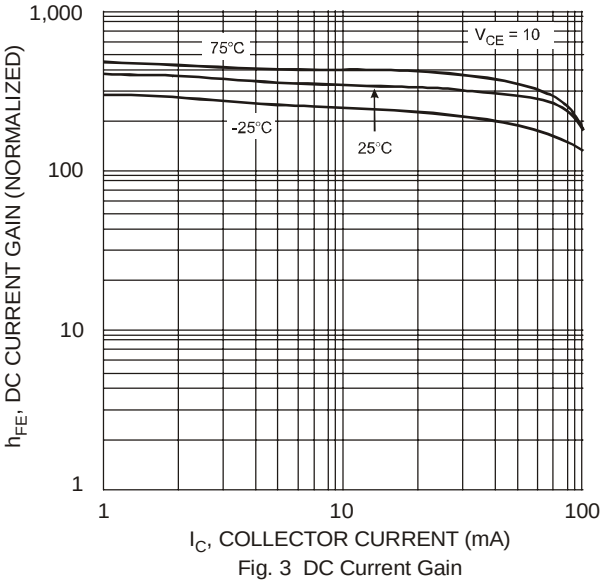


Fig. 3 DC Current Gain

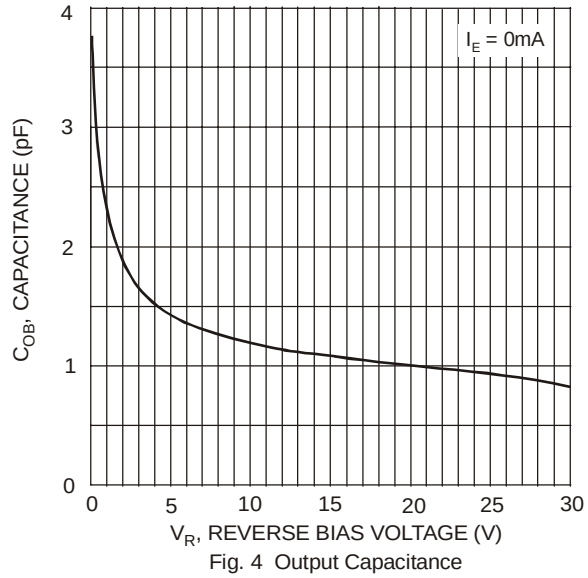


Fig. 4 Output Capacitance

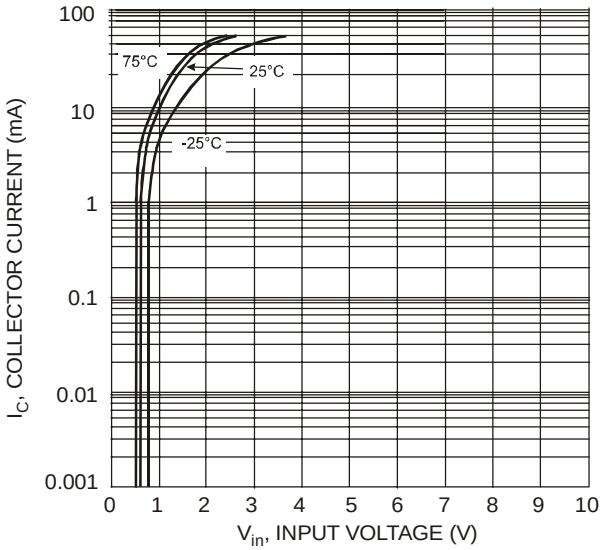


Fig. 5 Collector Current vs. Input Voltage

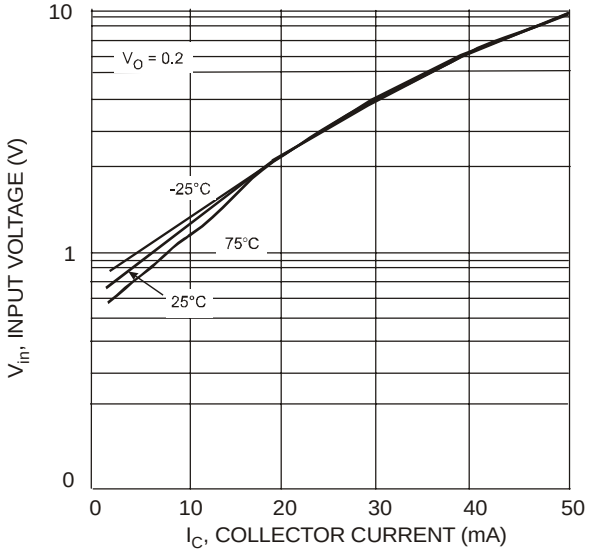


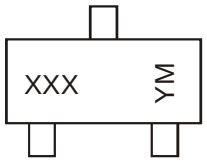
Fig. 6 Input Voltage vs. Collector Current

Ordering Information (Note 4 & 5)

Device	Packaging	Shipping
DDTC1xxTUA-7-F	SOT-323	3000/Tape & Reel
DDTC1xxTUA-13-F	SOT-323	10,000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



XXX = Product Type Marking Code, See Table on Page 1
YM = Date Code Marking
Y = Year ex: T = 2006
M = Month ex: 9 = September

Date Code Key

Year	2006	2007	2008	2009	2010	2011	2012
Code	T	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D